

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:  
SADAKA, MARIAM G., et al.  
Application No.: 10/029093  
Filed: December 21, 2001  
Docket No.: SC11464ZP

§ Patent No.: 6803248  
§  
§ Issue Date: October 12, 2004  
§  
§ Examiner: Long Pham  
§  
§ Group Art Unit: 2814  
§  
§

Title: A CHEMISTRY FOR ETCHING QUATERNARY INTERFACE LAYERS ON  
InGaAsP MOSTLY FORMED BETWEEN GaAs AND In<sub>x</sub>Ga(1-x) P LAYERS

Certificate of Submission

I hereby certify that this correspondence is being submitted to  
the U.S.P.T.O., Alexandria, VA.

Submitted electronically via EFS in accordance with  
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3-9-07

Pat Thomas

Signature

Pat Thomas  
Printed Name of Person Signing Certificate

Commissioner for Patents  
Alexandria, VA 22313

SUBMISSION OF CERTIFICATE OF CORRECTION

Dear Commissioner:

Enclosed is a Certificate of Correction listing error(s) in the subject patent. Since the errors appear to be on the part of the United States Patent Office, there should be no charge.

Claims 36-42 were added in an Amendment dated January 5, 2004. These additional claims were paid for as evidenced via the Patent Application Fee Determination Record.

2007-03-09  
Date

Respectfully submitted,

*Michael J. Balconi-Lamica*

Michael J. Balconi-Lamica  
Attorney for Applicant(s)  
Registration No. 34,291  
Telephone No. (512) 996-6839  
Facsimile No. (512) 996-6854

MAILING ADDRESS OF SENDER (Please do not use customer number below)

Freescale Semiconductor, Inc., Law Department  
7700 West Parmer Lane PL02, Austin, TX 78729

**UNITED STATES PATENT AND TRADEMARK OFFICE**  
**CERTIFICATE OF CORRECTION**

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PATENT NO.: 6803248  
APPLICATION NO: 10/029093  
DATE: 12/12/2004  
INVENTOR(S): SADAKA, MARIAM G. et al.

It is certified that error appears in the above-identified patent and that said Letters Patent are hereby corrected as shown below:

After Claim 5, insert dependent claims 36-42 which were added in an Amendment dated January 5, 2004

36. The method of claim 24, wherein the volumetric ratio of H<sub>2</sub>O to HC1 in the solution is greater than about 15:1.

37. The method of claim 24, wherein the volumetric ratio of H<sub>2</sub>O to HC1 in the solution is at least about 20:1.

38. The method of claim 36, wherein the mole ratio of H<sub>2</sub>O<sub>2</sub> to HC1 in the solution is within the range of about 1:12 to about 3:4.

39. The method of claim 36, wherein the mole ratio of H<sub>2</sub>O<sub>2</sub> to HC1 in the solution is within the range of about 1:12 to about 1:4.

40. The method of claim 37, wherein the mole ratio of H<sub>2</sub>O<sub>2</sub> to HCl in the solution is within the range of about 1:12 to about 3:4.

41. The method of claim 37, wherein the mole ratio of H<sub>2</sub>O<sub>2</sub> to HC1 in the solution is within the range of about 1:12 to about 1:4.

42. The method of claim 29, wherein the composition is selective to InGaP.

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